

Advanced High Speed Design

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May 12, 2022

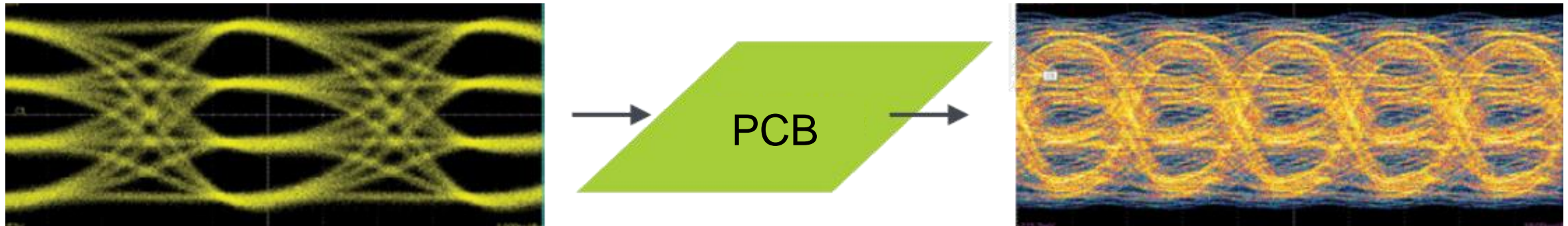
Agenda

- 1 Signal Integrity in High Speed PCBs
- 2 Channel Characterization
- 3 Analysis of Transmission Line Styles

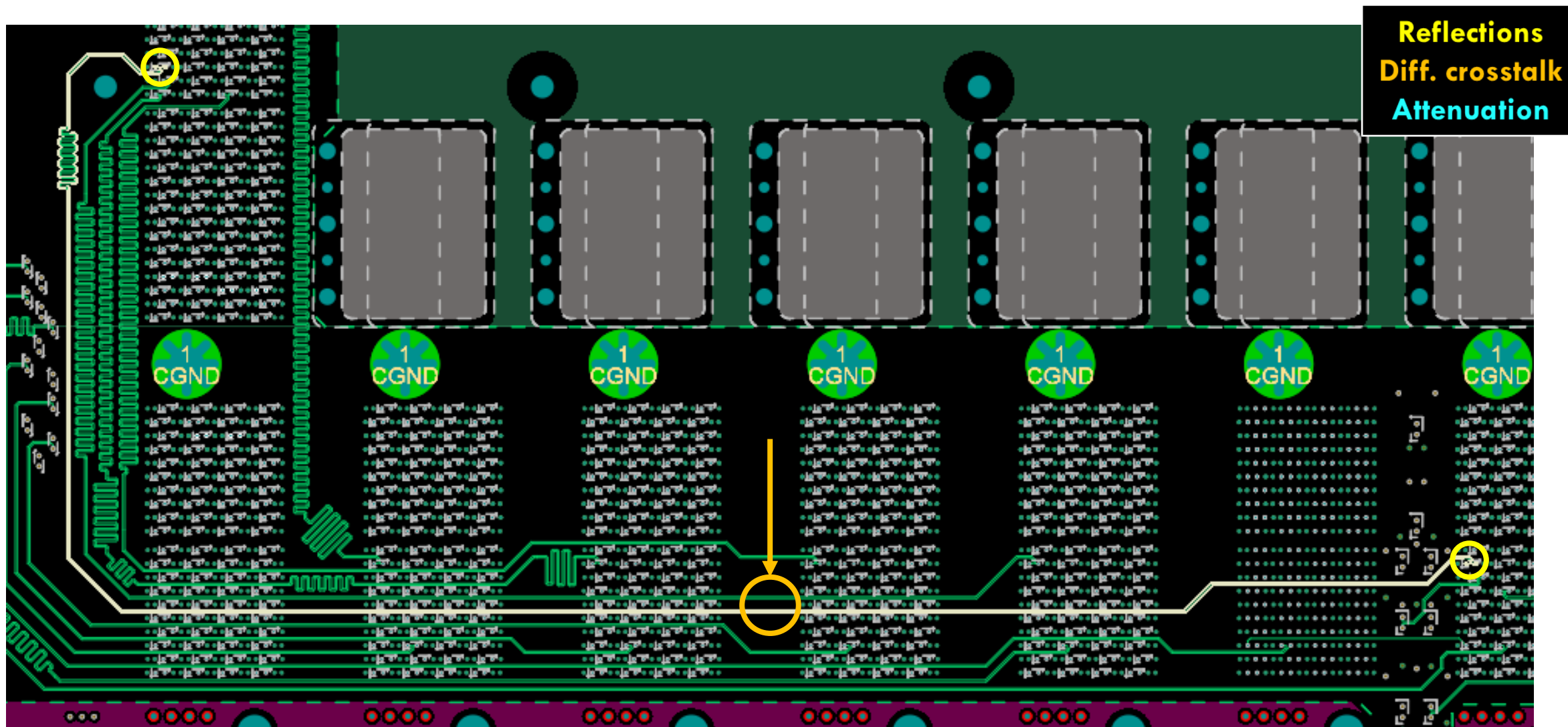
Signal Integrity Challenges in High Speed PCBs

- Most of what you do in high speed PCB design is intended to ensure signal integrity (SI).
- **Related:** Power integrity
- **Related:** Electromagnetic interference
- Determined by a few critical areas:
 - Stackup/material selection
 - Differential interconnect design and routing
 - Stable power system design
 - Noise coupling between interconnects

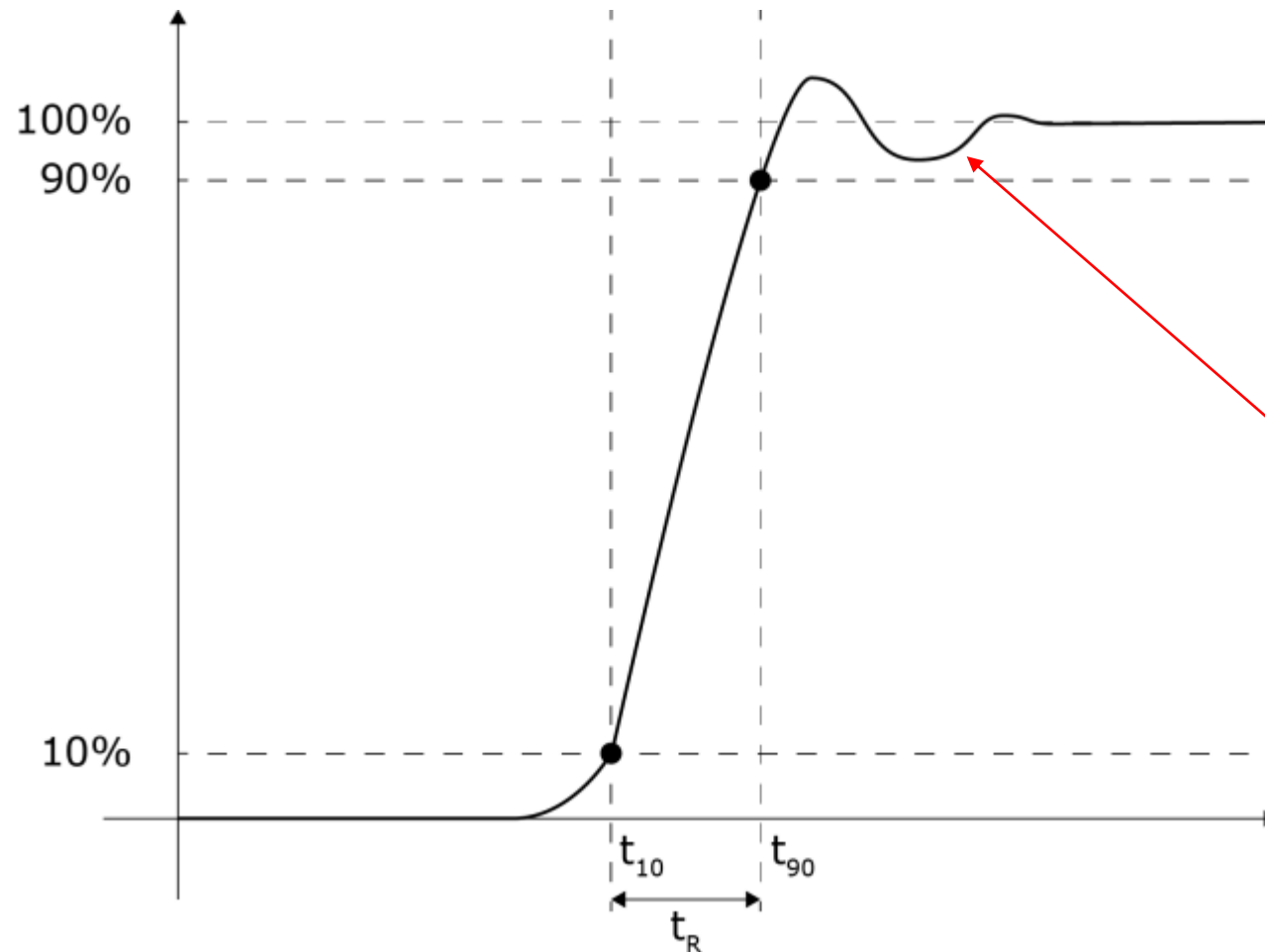
- Signals → Analyzed in the time domain
- Channels → Analyzed in the time or frequency domain
- Metrics: S-parameters, impedance, inter-symbol interference (ISI), jitter, channel operating margin (COM),...



Example with 56G channels on Eurocard backplane (6U)

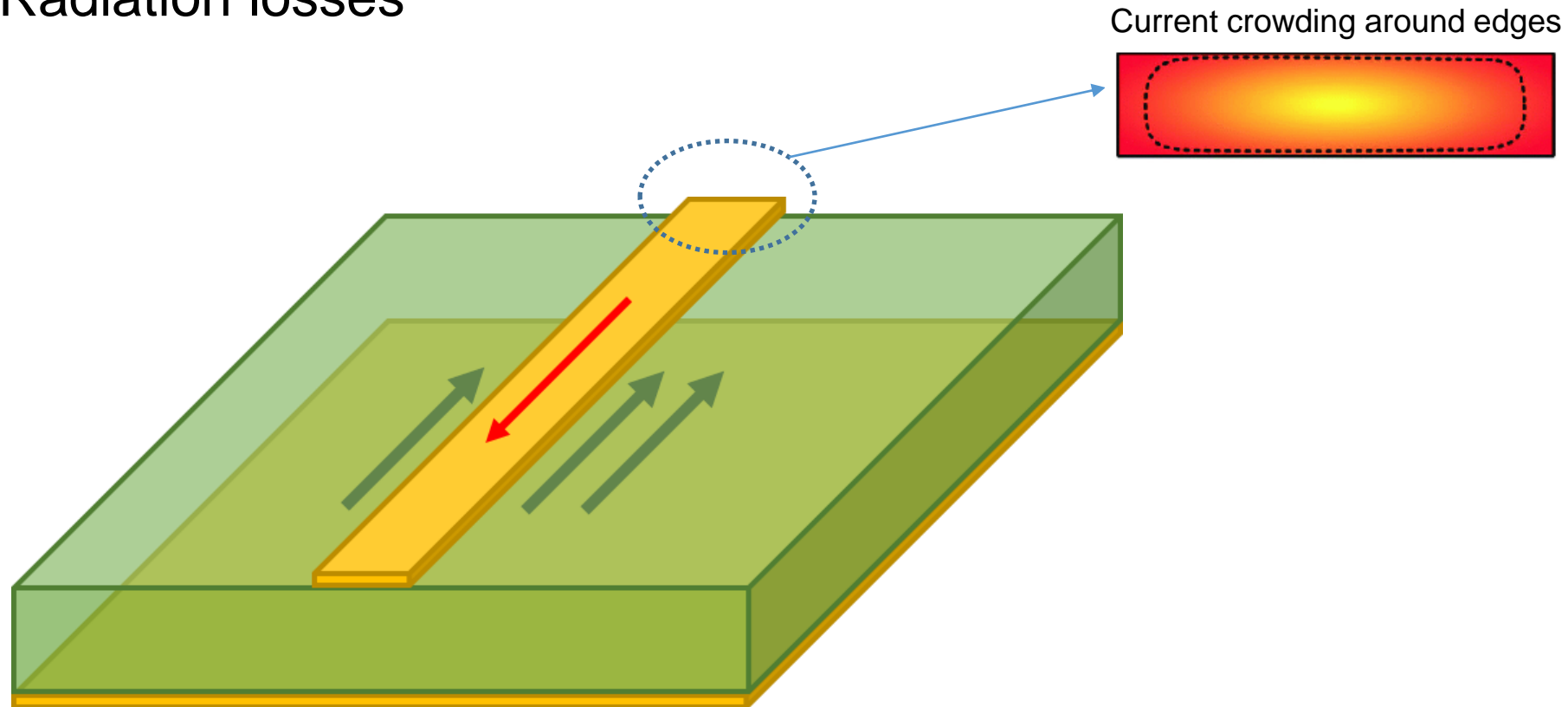


- Signal rise time ($\frac{dI}{dt}$ and $\frac{dV}{dt}$) governs electrical behavior

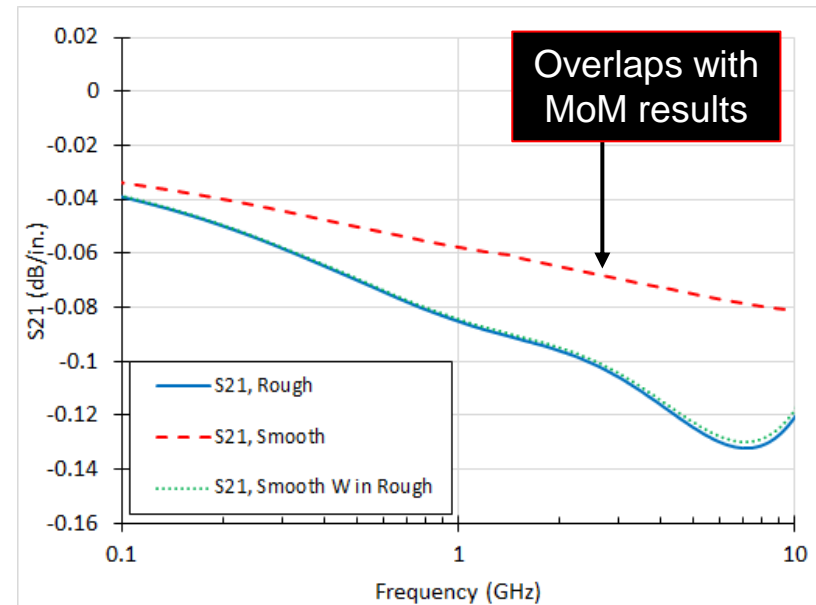
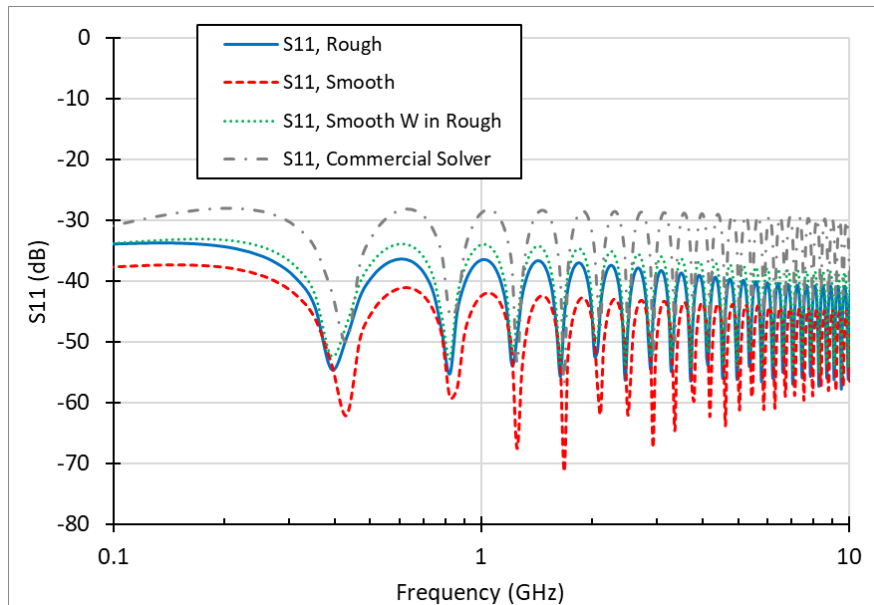
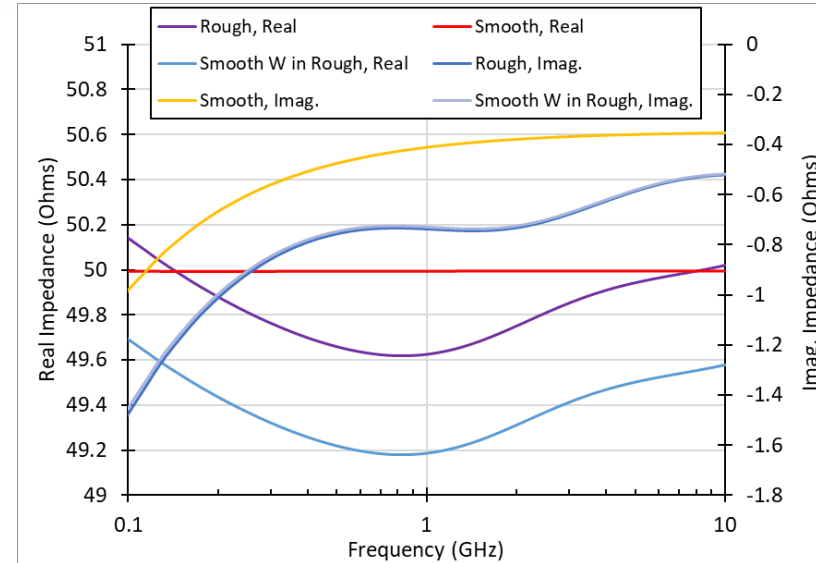


- Crosstalk
- Radiated emissions
- Measurement artifacts (Gibbs)
- Transient phenomena
- Resonant phenomena

- Dielectric losses
- Copper losses (DC, skin effect, roughness)
- Plating and solder mask create additional losses
- Radiation losses



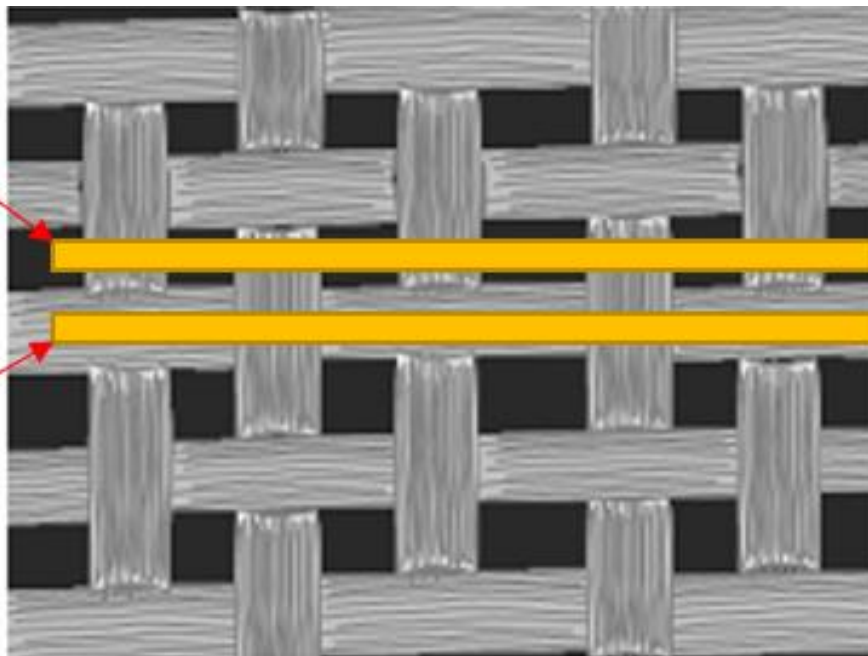
- **Rough line:** $W = 0.178$ mm (6.996 mil)
- **50 Ω Smooth line:** $W = 0.180$ mm (7.085 mil) \rightarrow No dispersion or skin effect
- **Smooth dispersion-less line:** $\epsilon = 4.171 + 0.0576i$ (@ 1 GHz)
- **Commercial MoM solver says 49.99 Ohms at 7.614 mils**



- Signal rise time can be used to find a very large length matching tolerance (sometimes this will be several cm)
- **However:** this assumes perfect channels!

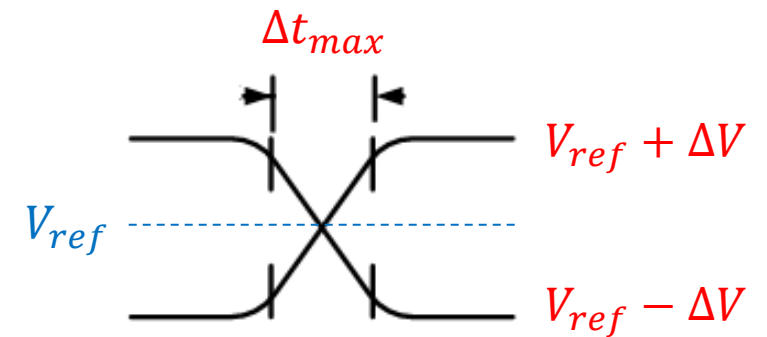
$$\epsilon_{resin} < \epsilon_{fiber}$$

Skew accumulates
in this trace



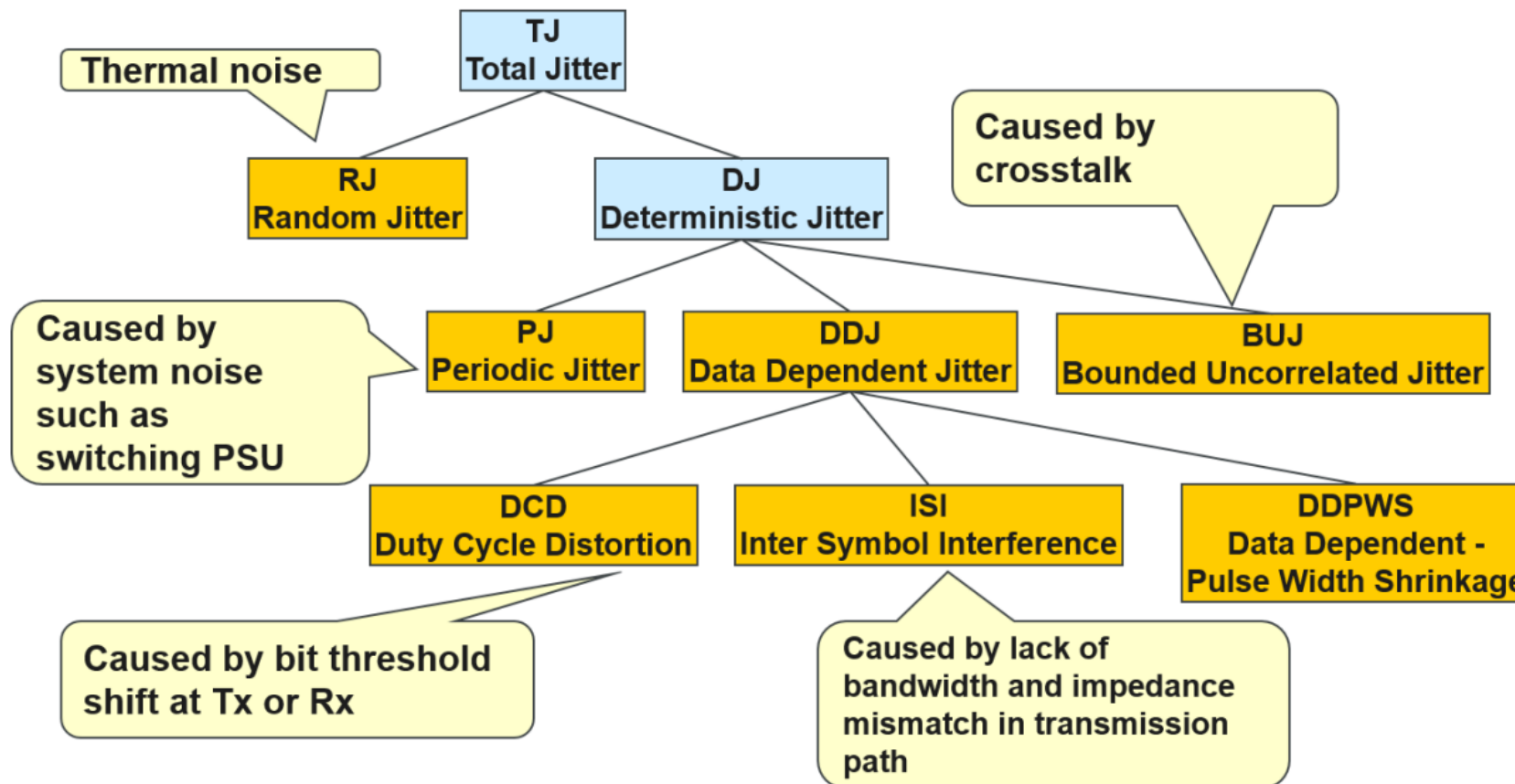
No skew in this trace

Still skew with perfect length matching!



What are the other sources of skew/jitter?

- Jitter is best defined as “the sum of all skews” (Steve Corrigan, Texas Instruments)



A stylized, dark blue graphic of grass or reeds, rendered with overlapping, curved blades, positioned in the upper right quadrant of the slide.

Channel Characterization

- Determine magnitude of SI problems
- Find potential cause of SI problems
- Determine course of action to eliminate the problem
- **Example:** Layer thickness and routing – should these be changed?
- **Example:** Prepreg vs. core order

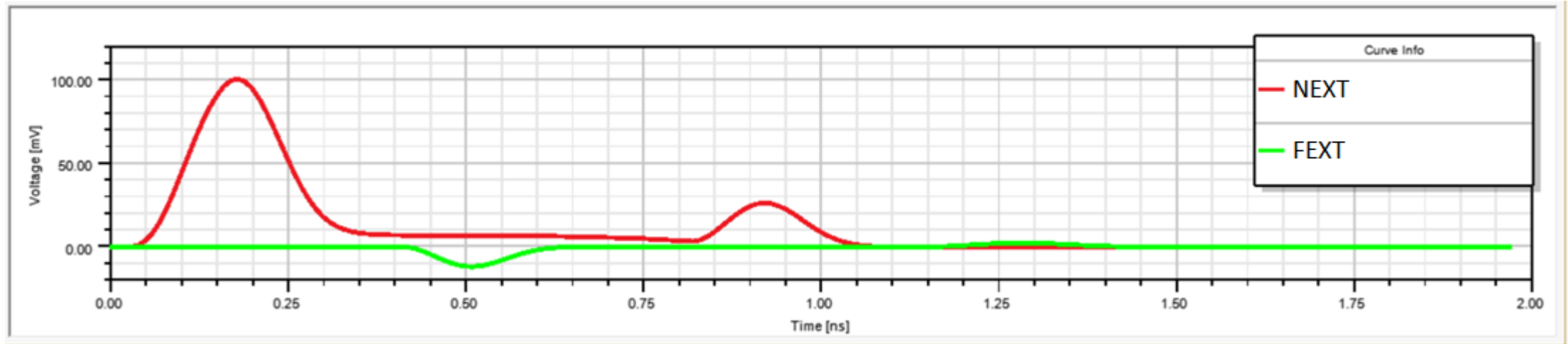
Analytical

- Numerical methods:
 - 2D field solvers w/BEM or MoM
 - 3D field solvers
 - SPICE
 - IBIS
- By hand with formulas or mixed formulas/tabulated data
- Dispersive losses → **requires wideband analysis**

Experimental

- Oscilloscope w/ eye diagram
- VNA (S-parameter measurements)
- Spectrum analyzer + arbitrary waveform generation
- **Probe and instrument characteristics must be known**

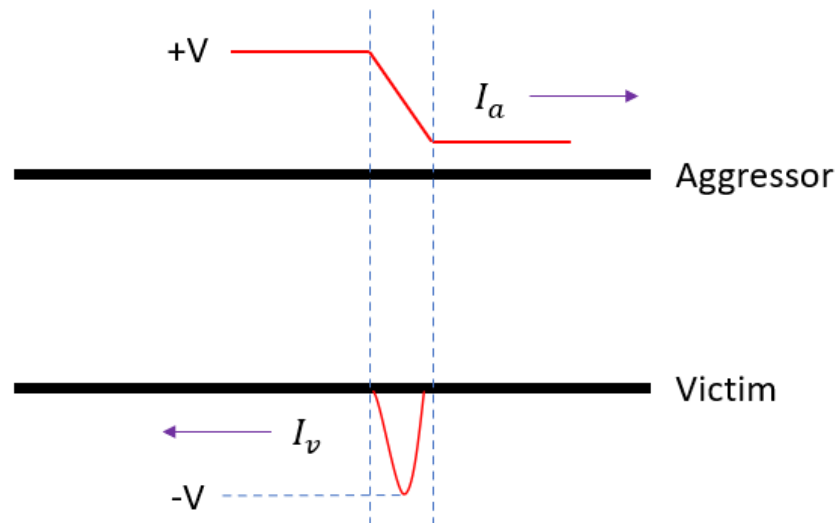
- Near-end and far-end crosstalk (NEXT and FEXT)



Inductive:

$$V_c = -L_M \frac{dI_A}{dt}, I_c = \frac{V_c}{Z_0}$$

Capacitive:

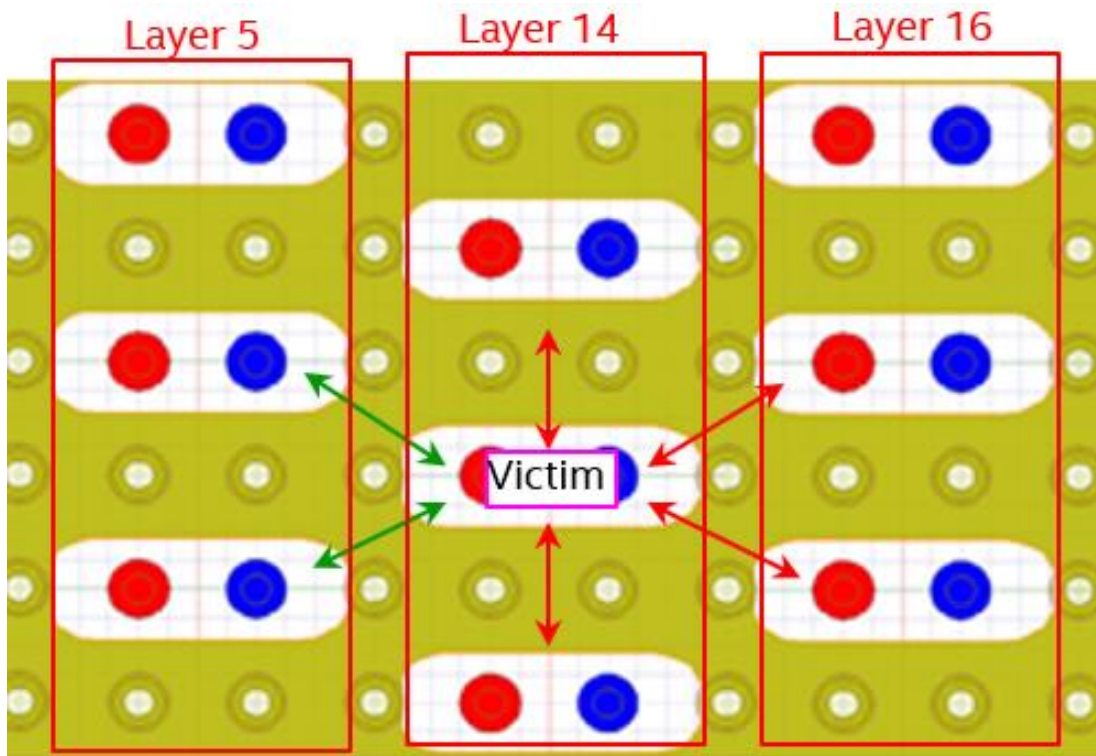
$$I_c = C_M \frac{dV_A}{dt}, V_c = I_c Z_0$$


$$NEXT = \frac{1}{4} \left(\frac{length}{vel \cdot t_{rise}} \right) \cdot \left(\frac{C_M}{C_L} + \frac{L_M}{L_L} \right)$$

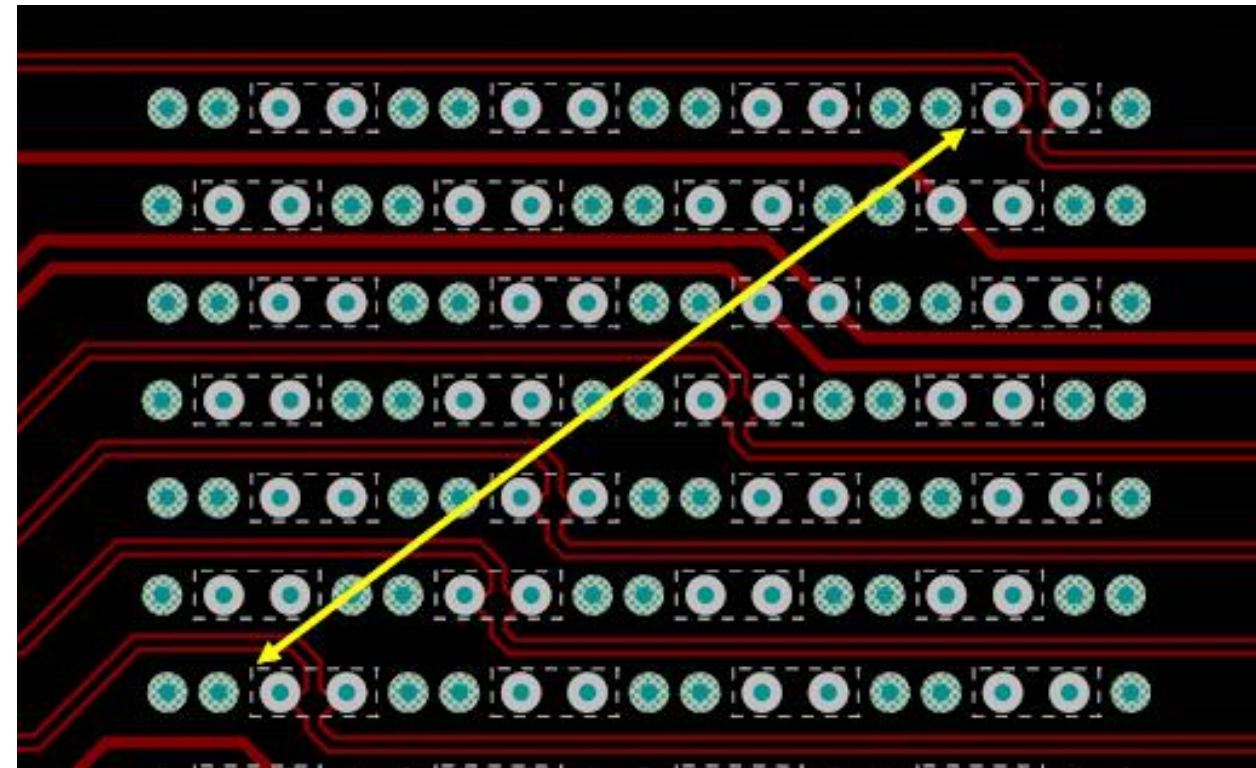
Always ≤ 1

$$FEXT = \frac{1}{2} \cdot \left(\frac{length}{vel \cdot t_{rise}} \right) \cdot \left(\frac{C_M}{C_L} - \frac{L_M}{L_L} \right)$$

- Differential pairs can exhibit crosstalk between each other
- For FPGAs: Plan to stagger vias (same strategy used in OpenVPX backplanes), interleave ground vias

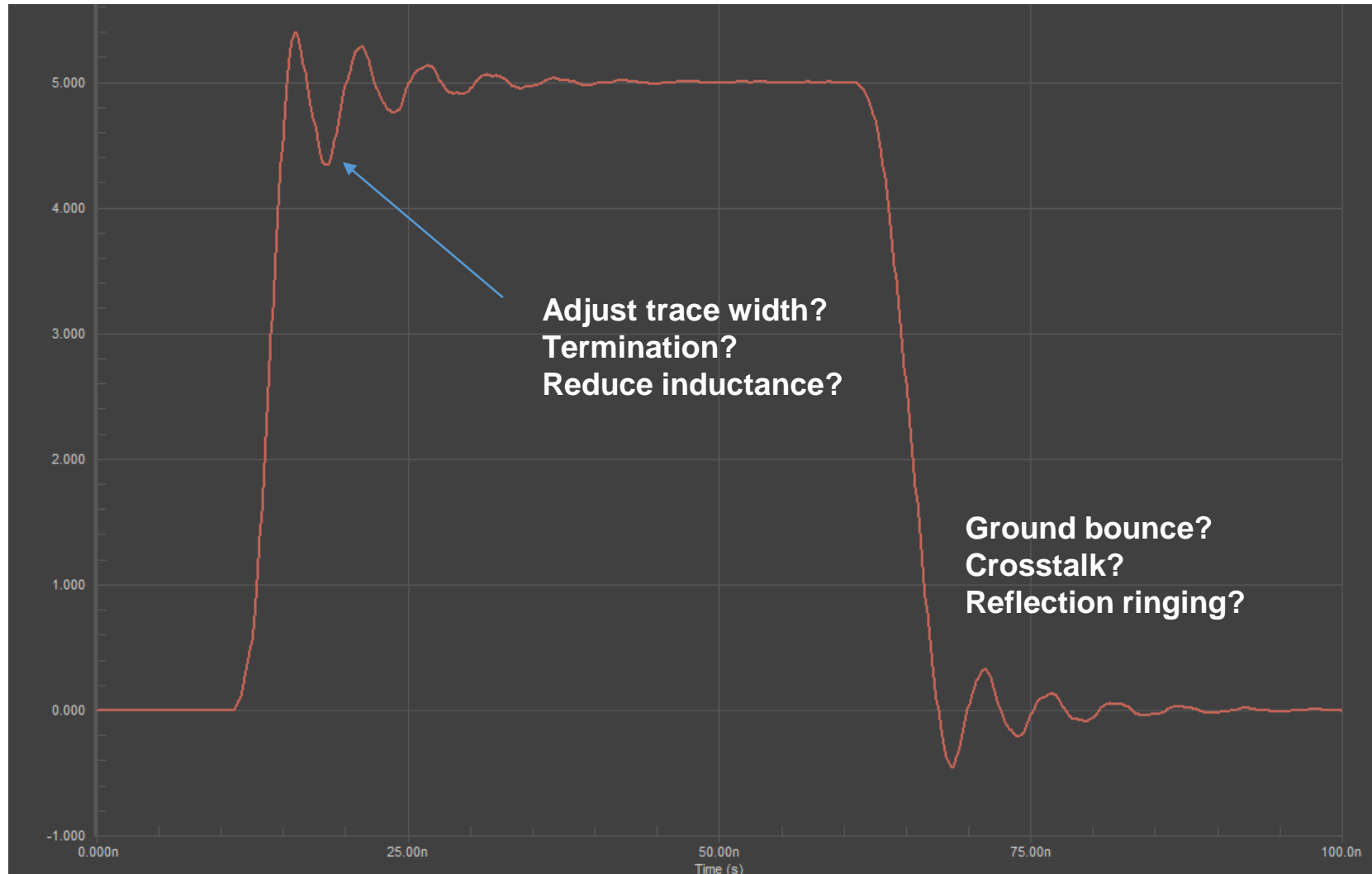


Breakout on FPGA



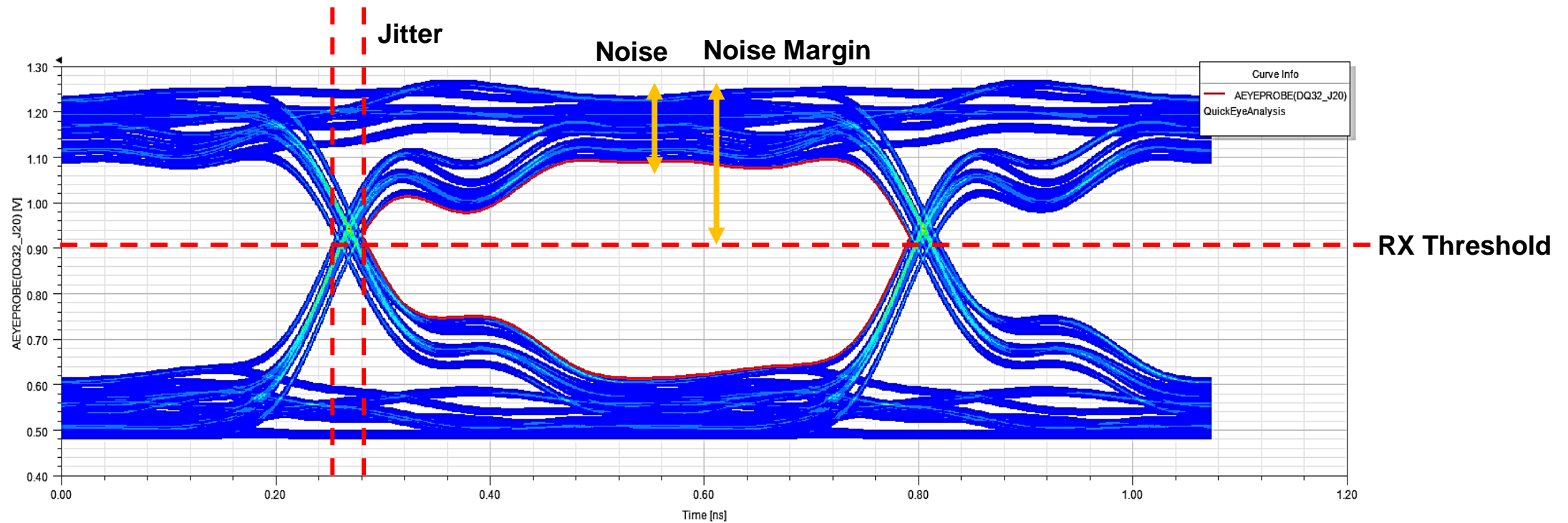
Bus routing on backplane

- Can be calculated with same 2D solver as in crosstalk simulations

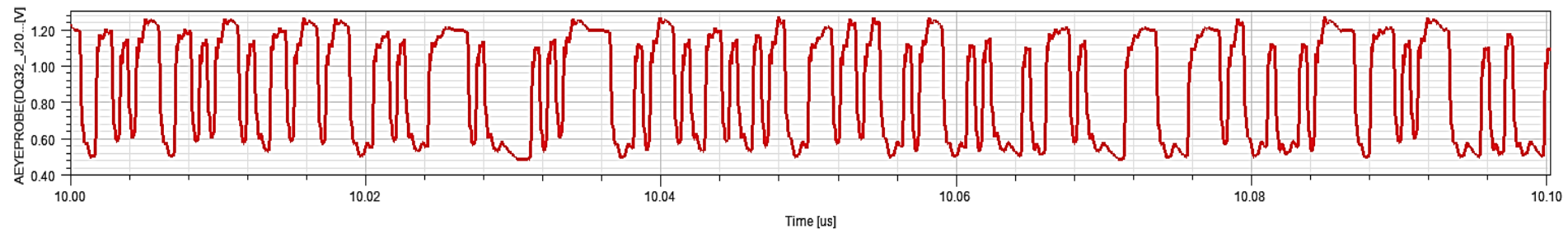


- Identify noise and jitter → estimate BER and SNR

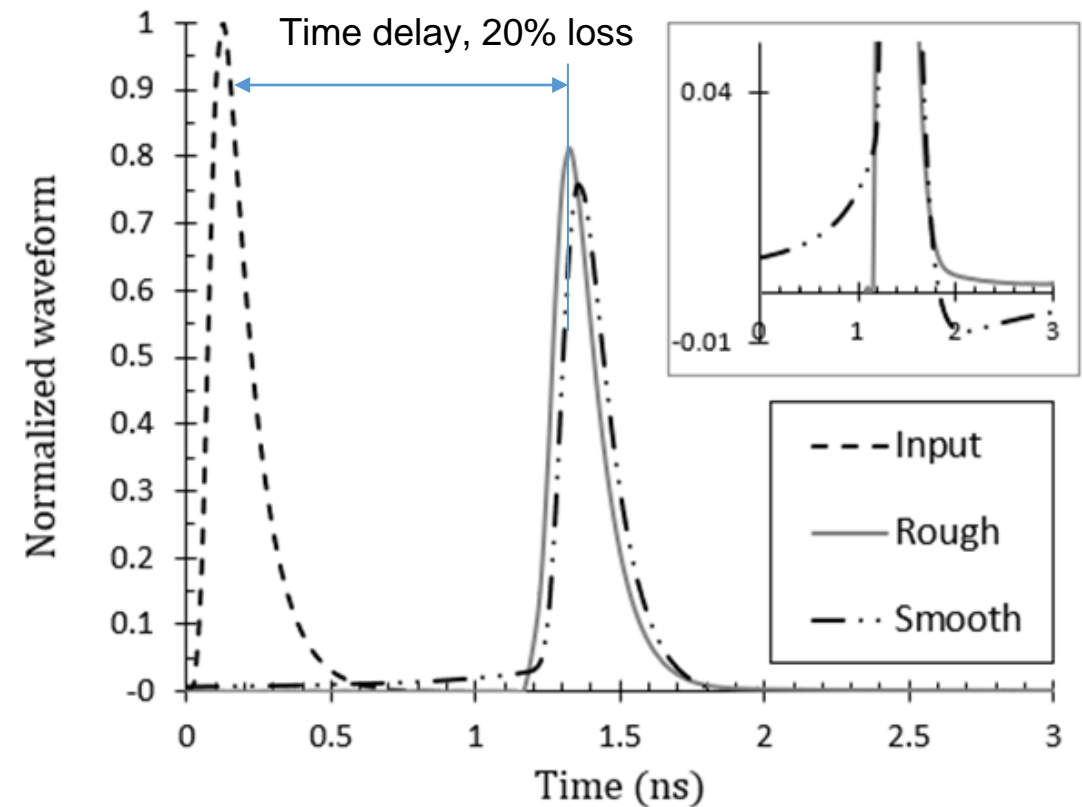
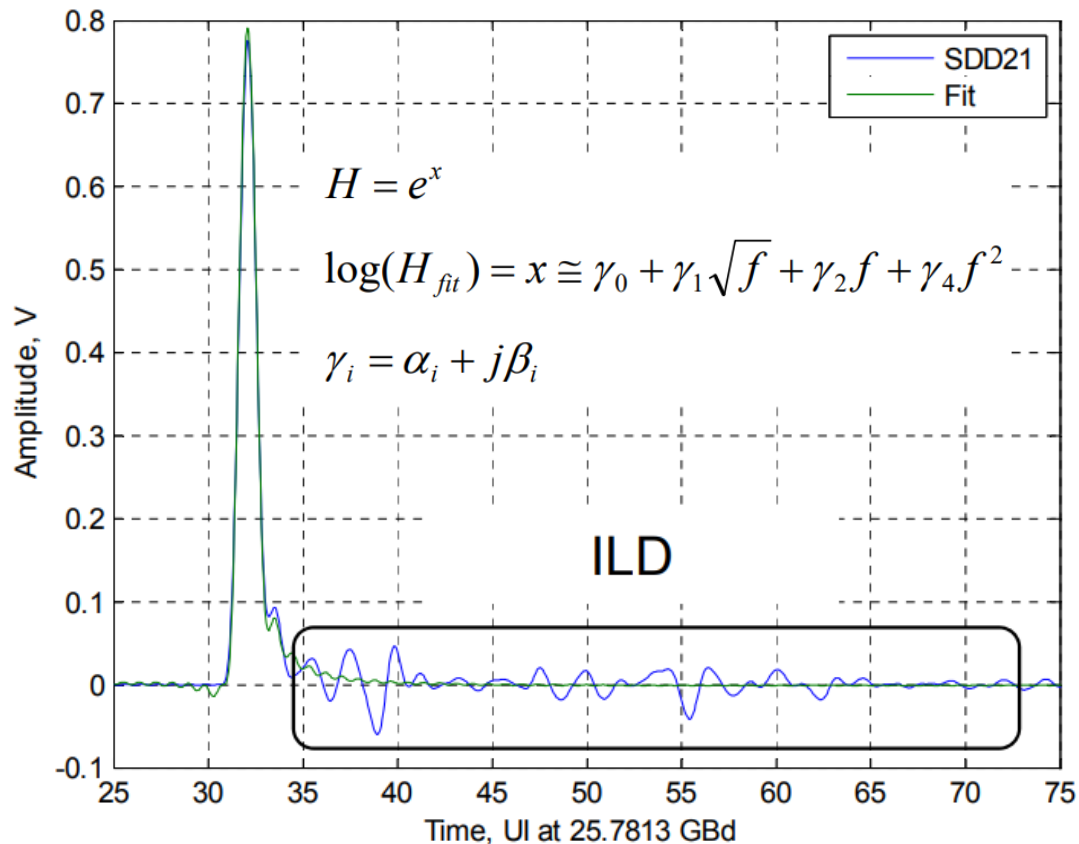
Eye Diagram



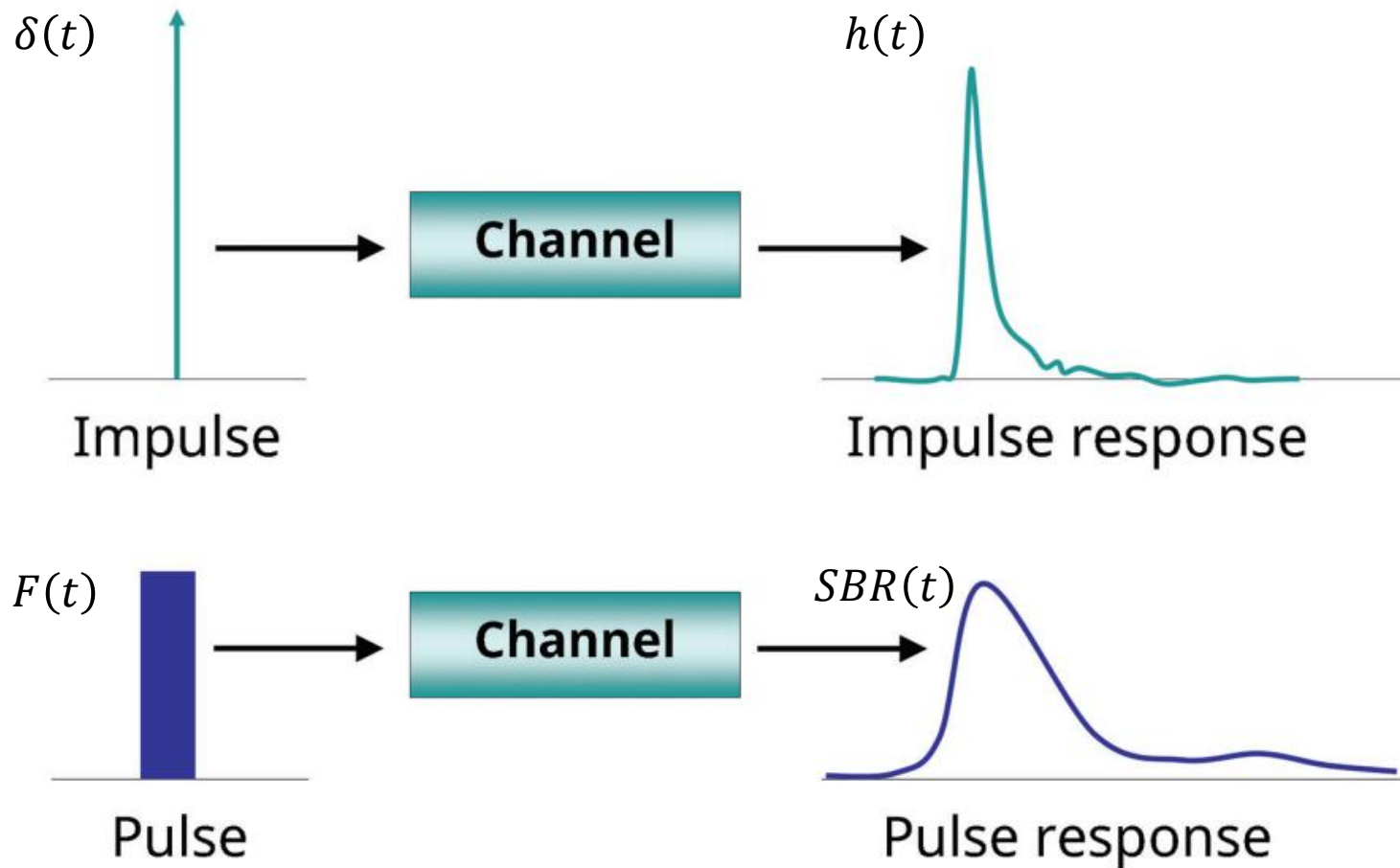
PRBS



- Identify non-causal effects in channel models
- Identify reflections on the tail-end of impulse response



- Based on channel simulation: determine impulse response, use to calculate single-bit response (SBR)



$$SBR(t) = \int_{-\infty}^{\infty} F(t')h(t - t')dt'$$

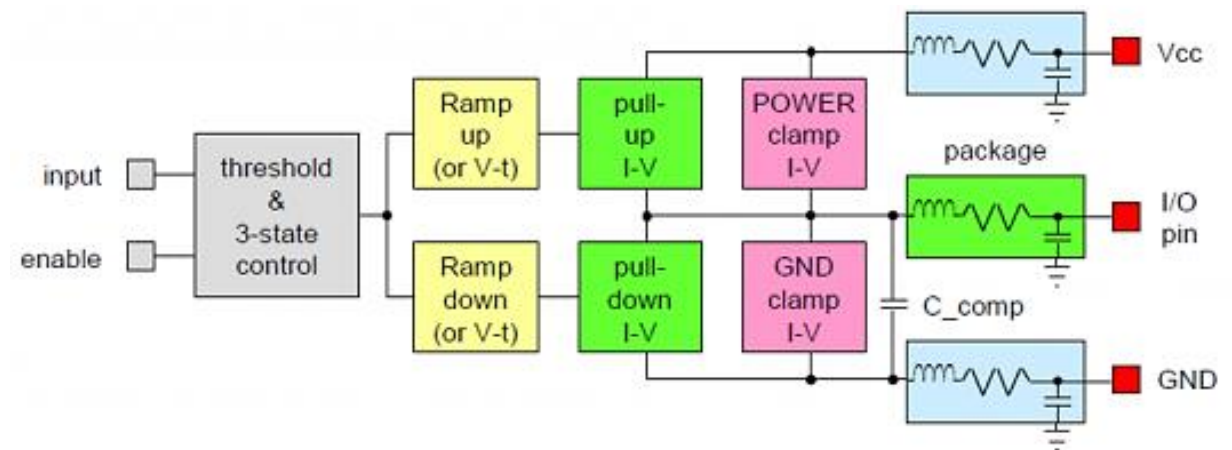
- Behavioral model, faster than SPICE
- Assign model behavior by pin
- Available from manufacturers

Pin Models

Model Name	Model Type
RDY	OPEN_SINK
DQ0	IO
ACC	INPUT
RSTB	INPUT
WEB	INPUT
OEB	INPUT

Model Type: Typical Case

- Models signal behavior on the output buffer in a logic circuit





Analysis of Transmission Line Styles

$$Z_0 = \sqrt{\frac{R+i\omega L}{G+i\omega C}}, \quad \gamma = \sqrt{(R+i\omega L)(G+i\omega C)} \rightarrow v = \frac{1}{\sqrt{LC}} \text{ (lossless)}$$

	<p>Coplanar microstrip</p> <p>Coplanar microstrip w/ ground</p>	$v = \frac{c}{\sqrt{\epsilon_{R,eff}}}$	<ul style="list-style-type: none"> • Lower losses, copper pour allows for thinner 50 Ohm traces
	<p>Microstrip</p>	$v = \frac{c}{\sqrt{\epsilon_{R,eff}}}$	<ul style="list-style-type: none"> • Lower losses, wider traces
	<p>Symmetric stripline</p> <p>Asymmetric stripline</p>	$v = \frac{c}{\sqrt{\epsilon_R}}$	<ul style="list-style-type: none"> • Higher losses, but traces can be much thinner than on the surface layer

- Transmission lines: $Z_0 = \sqrt{\frac{R+i\omega L}{G+i\omega C}}$, $\gamma = \sqrt{(R + i\omega L)(G + i\omega C)}$

$$R(\omega) = R_{DC} + \sqrt{\omega} R_s \quad L(\omega) = L_\infty + \frac{R_s}{\sqrt{\omega}}$$

$$G(\omega) = \omega C(\omega) \tan \delta(\omega) \quad C(\omega) = K_g \epsilon_R(\omega) \epsilon_0$$

- Dielectric constant: $\epsilon = \epsilon_R(\omega) + i\epsilon_I(\omega)$, $\tan \delta = \frac{-\omega \epsilon_I(\omega) - \sigma_{sub}}{\omega \epsilon_R}$
- Need causal models or data for:

Dielectric constant: $\epsilon(\omega)$

Copper roughness: $K(\omega)$

Electrical parameters: $R(\omega), L(\omega)$

- General definition: $H(f) = \frac{V_L}{V_S} = \frac{Z_L}{AZ_L + B + CZ_S Z_L + DZ_S}$

$$\begin{bmatrix} A & B \\ C & D \end{bmatrix} = \begin{bmatrix} \cosh(\gamma l) & Z_0 \sinh(\gamma l) \\ \frac{\sinh(\gamma l)}{Z_0} & \cosh(\gamma l) \end{bmatrix}$$

- Three cases that can be derived by hand from ABCD parameters:

$$Z_S = 0, \text{ load terminated with } Z_T: H(s) = \frac{1}{\cosh \gamma l (1 + Z_0 \left(\frac{1 + sZ_T C_L}{Z_T} \right) \tanh \gamma l)}$$

$$Z_S = Z_0, \text{ load terminated with } Z_T: H(s) = \frac{e^{-\gamma l}}{1 + Z_0 \left(\frac{1 + sZ_T C_L}{Z_T} \right)}$$

$$\text{Unterminated } Z_S = 0, Z_L = \frac{1}{sC_L}: H(s) = \frac{1}{\cosh \gamma l (1 + Z_0 s C_L \tanh \gamma l)}$$

- Approximate the square root: $\gamma = \sqrt{(R + i\omega L)(G + i\omega C)}$
- Take the real part of the result and break into conductor + dielectric

$$\alpha_{total} = \alpha_{conductor} + \alpha_{dielectric}$$

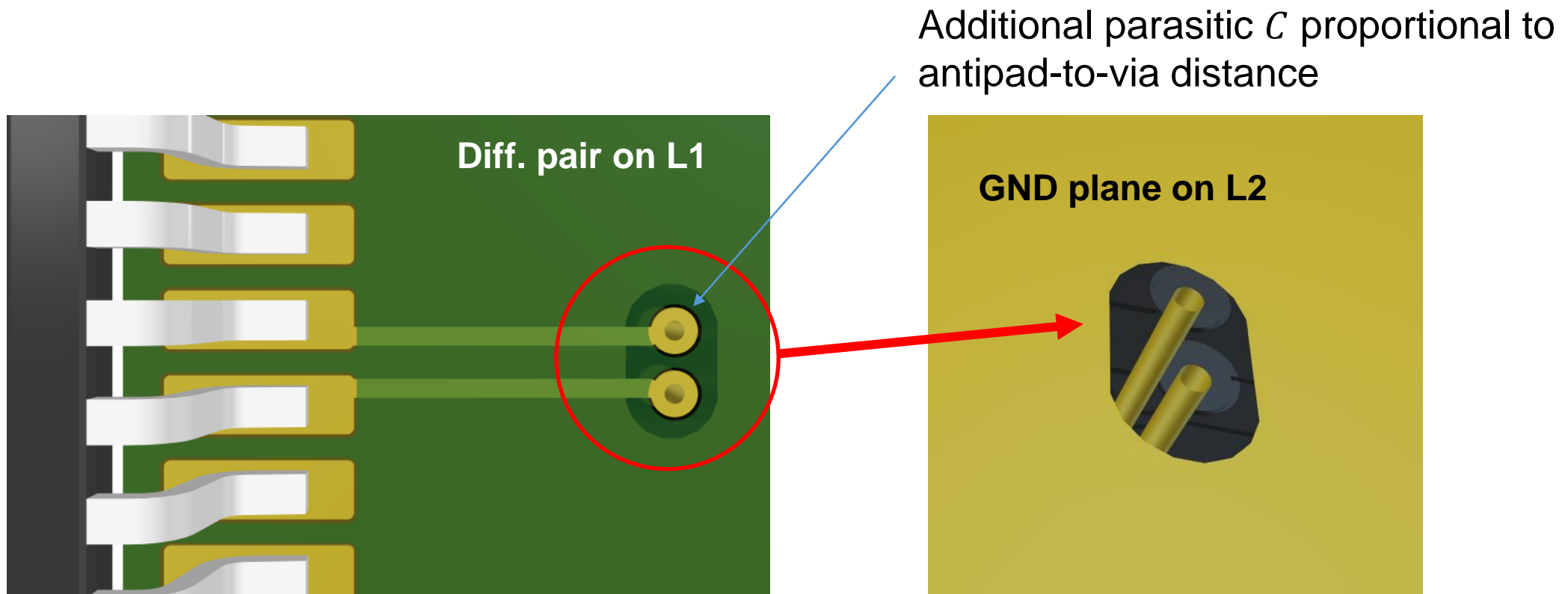
$$\alpha_{dielectric} = 4.34(\omega CZ_0 \tan \delta) \text{ in dB/length}$$

$$\alpha_{conductor} = 4.34 \left(\frac{R_{DC} + \sqrt{\omega K(\omega) R_s}}{Z_0} \right) \text{ in dB/length,}$$

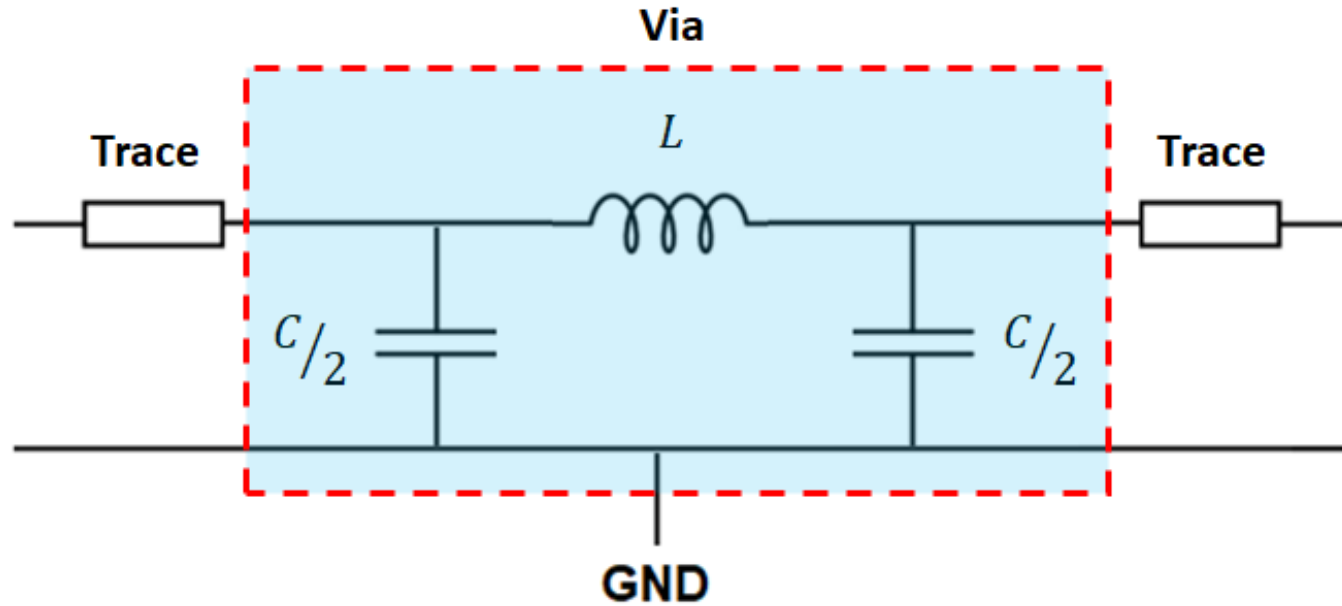
4.12 mil dielectric thickness,
unmodified Dk = 4.17/Df = 0.014

	$\alpha_{dielectric}$	$\alpha_{conductor}$ (smooth)	$\alpha_{conductor}$ (rough, Hammerstad)	$\alpha_{conductor}$ (rough, Cannonball-Huray, $a = 2 \mu m, H = 5 \mu m$)
Microstrip, 1 GHz	~0.059 dB/inch	~0.053 dB/inch	~0.080 dB/inch	~0.077 dB/inch
Microstrip, 10 GHz	~0.585 dB/inch	~0.14 dB/inch	~0.22 dB/inch	~0.25 dB/inch
Stripline, 1 GHz	~0.067 dB/inch	~0.13 dB/inch	~0.21 dB/inch	~0.19 dB/inch
Stripline, 10 GHz	~0.677 dB/inch	~0.35 dB/inch	~0.53 dB/inch	~0.63 dB/inch

- Antipad shape and size creates parasitic capacitance
- Place with stitching vias to control parasitics



- A simple model for vias and antipads



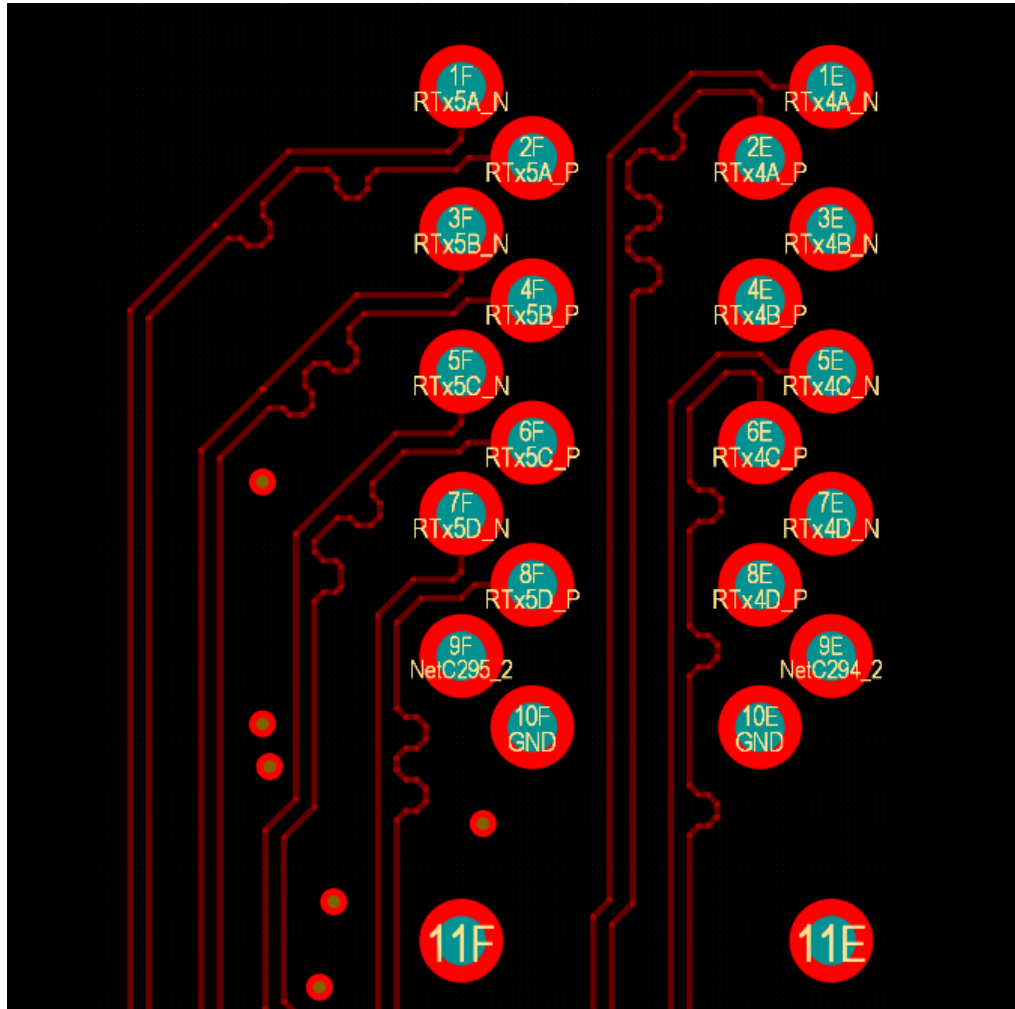
D_1 = pad diameter
 D_2 = antipad diameter
 l = via length
 d = via barrel diameter

$$f_{3dB} = \frac{1}{\sqrt{LC}}$$

$$L_{via} \approx 5.08l \left(\ln \left(\frac{4l}{d} \right) + 1 \right)$$

$$C_{via} \approx \epsilon_R \sqrt{2} \left(\frac{D_1 l}{D_2 - D_1} \right)$$

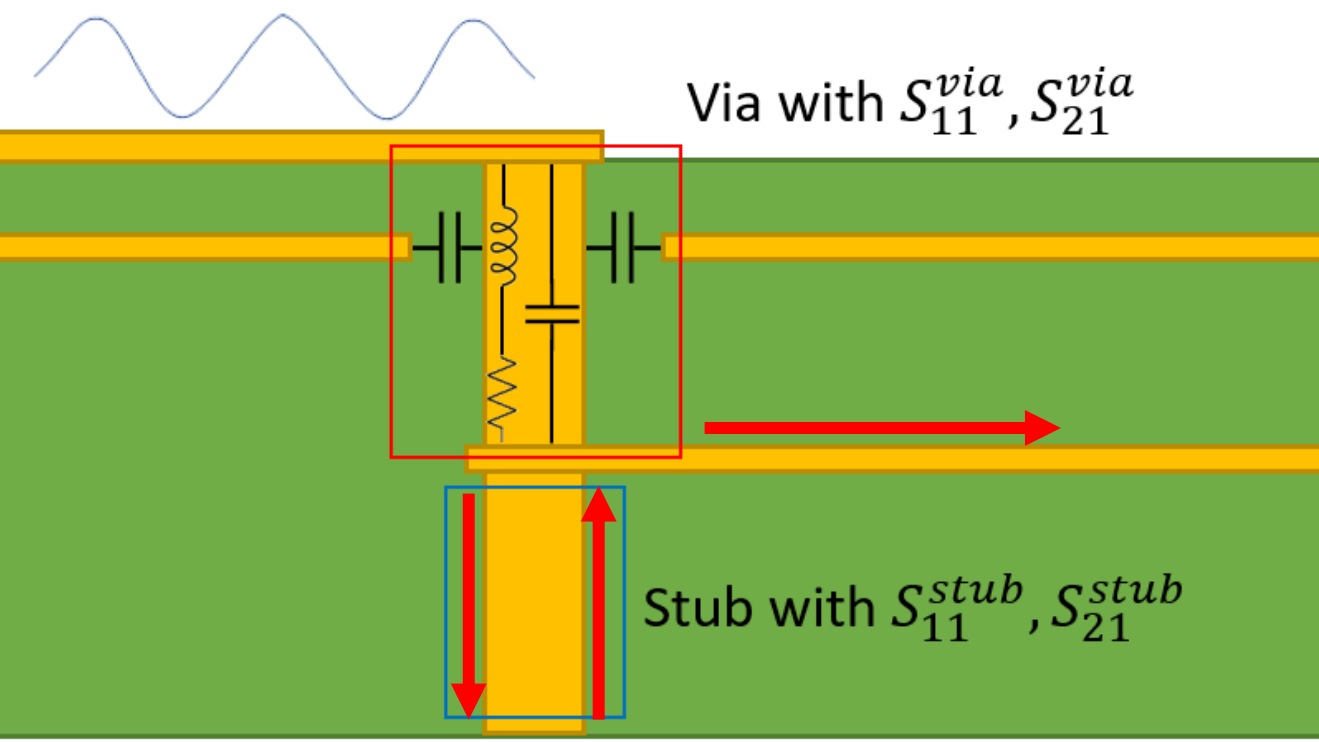
- Add length matching sections near inhomogeneity if possible



Frequency	FCC Class A	FCC Class B
<1.7 MHz*	40 uA	10 uA
1.7 - 30 MHz*	120 uA	10 uA
30 MHz**	24 uA	8 uA
50 MHz**	14 uA	5 uA
100 MHz**	11 uA	3.5 uA

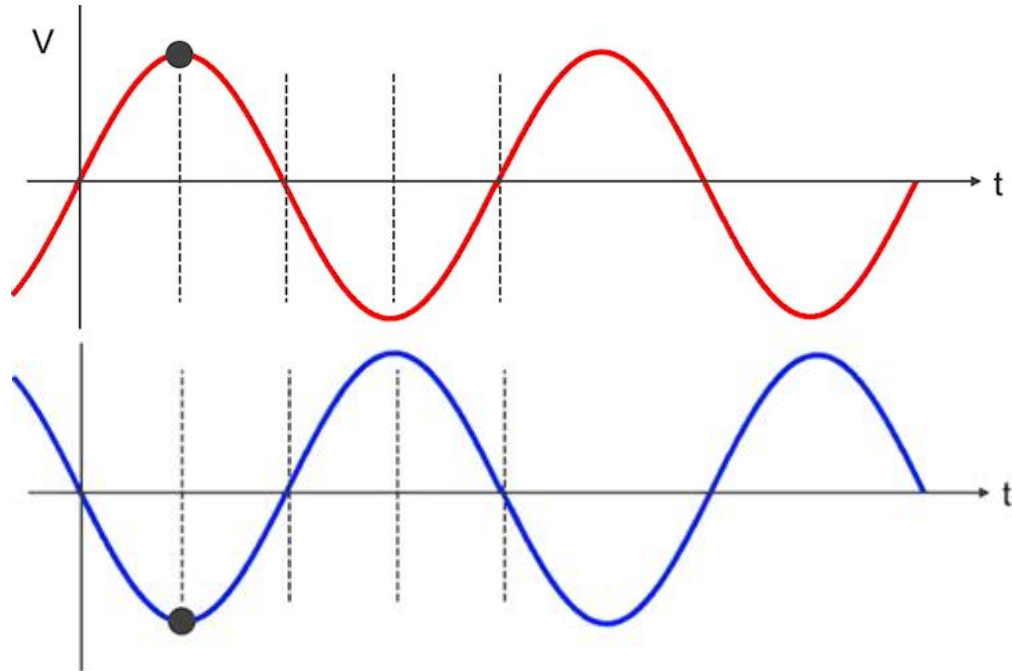
* Based on Conducted Emission Limits

** Based on Radiated Emission Limits



$$\Delta\phi = 2\pi \left(\frac{L_{via} f \sqrt{Dk_{eff}}}{c} \right)$$

Signal destroyed whenever $\Delta\phi = 180^\circ$

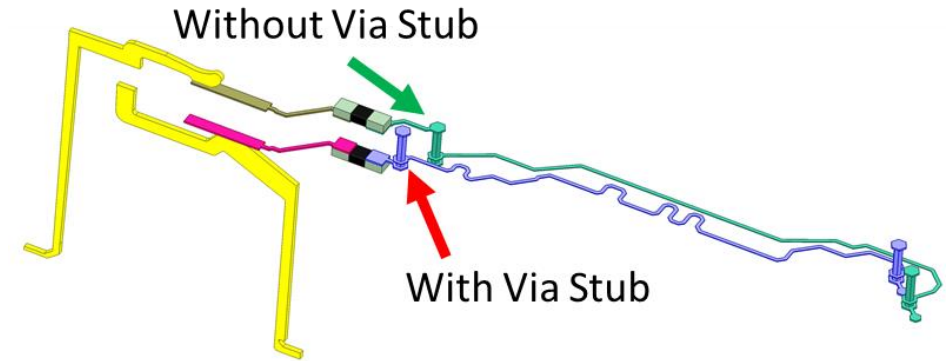
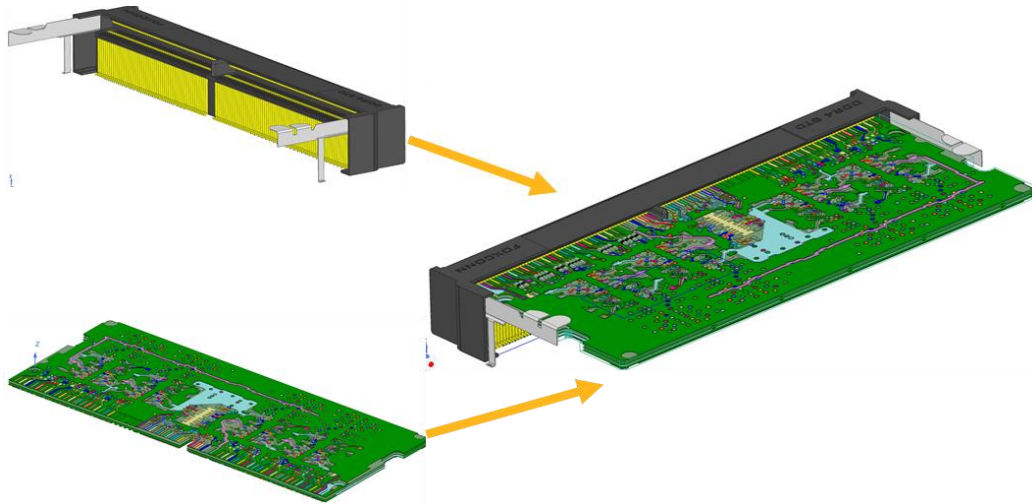


Low f $Z_{via} \approx i\omega L + R_{DC} + \sqrt{\omega}(1 + i)K(\omega)R_{skin}$

High f : Treat as a resonator (next slide), use input impedance

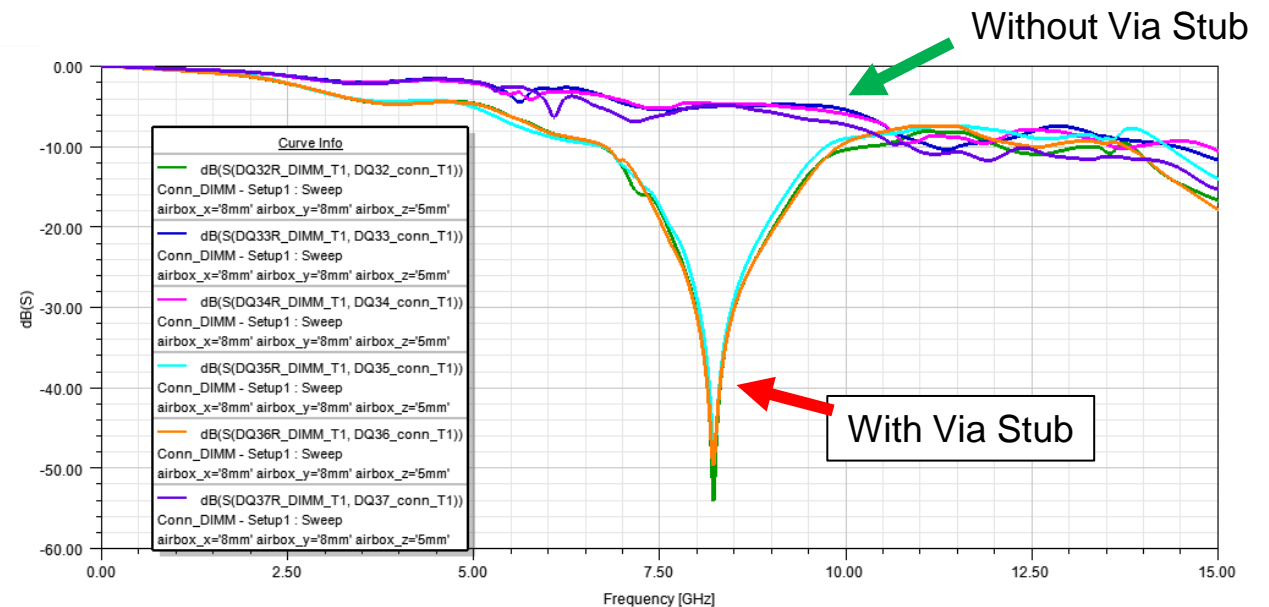
0.1 mm stub length: okay for signals up to roughly 150 GHz (typical FR4 substrate)

- When should stubs be removed?



- Stubs act like transmission lines:

$$f_n = \frac{c_{vacuum}}{\lambda_n \sqrt{Dk_{eff}}}, \quad n = 1, 3, 5, \dots$$

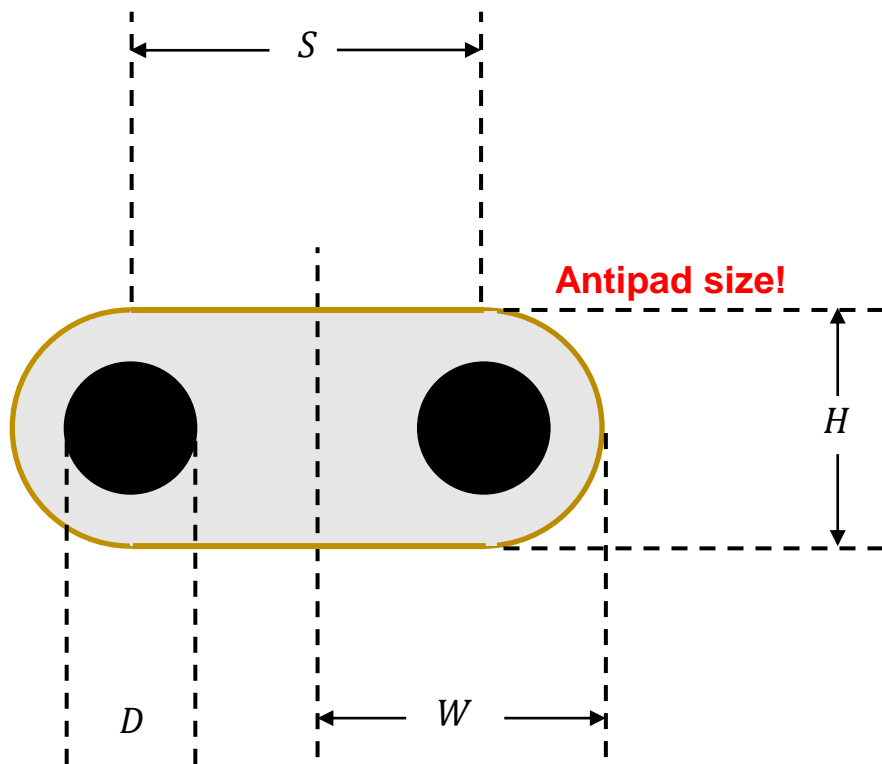


- Stubs create destructive interference at quarter wavelength resonances:

$$f_n = \frac{c_{vacuum}}{\lambda_n \sqrt{Dk_{eff}}}$$

$$\lambda_n = \frac{4L}{n}, \quad n = 1, 3, 5, \dots$$

$$Dk_{eff} = \left(\frac{Dk_{tr} + Dk_z}{2} \right) \frac{\ln \left(\frac{S}{D} + \sqrt{\left(\frac{S}{D} \right)^2 - 1} \right)}{\ln \left(\frac{W+H}{2D} \right)}$$



$$Dk_z \sim 1.2 Dk_{tr}$$

$$L_{max} [mils] \approx \frac{840}{GBaud * \sqrt{Dk_{eff}}}$$

Via delay:

$$t_{via} = \frac{L_{via} \sqrt{Dk_{eff}}}{c_{vacuum}}$$

- Stubs create destructive interference at quarter wavelength resonances:

Preferred



Minimal stub
equal to layer
thickness

Not preferred



Long stub may
limit bandwidth

Backdrilled



Leftover stub
might be **longer**
than the bottom
layer thickness



Thank You!

Stay tuned for our Altium Designer demonstration.